BCH65S04D3

Silicon Carbide Schottky Diode

650V, 4A



Description

BCH65S04D3 utilizes Bestirpower's advanced silicon carbide diode technology. This technology combines the benefits of excellent low forward voltage and robustness. Consequently, the family is suitable for application requiring high power efficiency.

Features

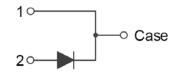
V _{RRM}	I _F	T _c	Q _c	
650 V	4 A	154 ℃	9.5 nC	

- High-speed switching
- Low heat dissipation requirements
- Reduce size and cost of the system
- Reduced EMI
- Higher system reliability due to lower operating temperaturest

Applications

- Switch mode power supply
- Solar inverter
- Data Center
- Uninterruptible power supply









Absolute Maximum Ratings (T_C = 25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive Peak Reverse Voltage		650	V
	Forward Current	T _C = 25°C	13	Α
I _F		T _C = 135°C	6	А
		T _C = 154°C	4	А
I _{F,SM}	Non-Repetitive Forward Surge Current	$T_C = 25^{\circ}C$, $t_p = 10 \text{ ms}$	39	Α
		$T_C = 110^{\circ}C, t_p = 10 \text{ ms}$	32	Α
I _{F,RM}	Repetitive Peak Forward Surge Current	$T_C = 25^{\circ}C$, $tp = 10 \text{ ms}$	34	Α
l ² dt value	∫l²t	$T_C = 25^{\circ}C$, $t_p = 10 \text{ ms}$	7	A ² s
		$T_C = 110^{\circ}C, t_p = 10 \text{ ms}$	5	A ² s
P _{tot}	Power Dissipation	T _C = 25°C	61	W
		T _C = 110°C	27	W
		T _C = 150°C	10	W
T_J , T_{STG}	Operating Junction and Storage Temperature		-55 to +175	°C



Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Typ.	2.44	°C/W

Electrical Characteristics (T_C = 25°C unless otherwise noted)

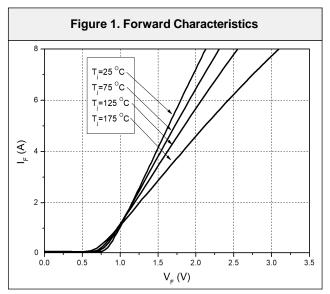
Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _{DC}	DC blocking voltage		650			V
V _F	Forward Voltage	I _F =4A,T _J =25℃	1	1.35	1.7	V
		I _F =4A,T _J =175℃	-	1.7	1.9	
I _R	Reverse Current	V _R = 650 V, T _J = 25°C	-	1	20	μA
		V _R = 650 V, T _J = 175°C	-	12	100	
Q _C	Total Capacitive Charge	V _R = 400 V, T _J = 25°C	-	9.5	-	nC
C Tot	Total Capacitance	V _R = 0 V, f = 1MHz	-	185	-	pF
		V _R = 200 V, f = 1MHz	1	19	1	
		V _R = 400 V, f = 1MHz	-	16.7	1	
Ec	Capacitance Stored Energy	V _R = 400 V, T _C = 25°C	1	2.4	1	μJ

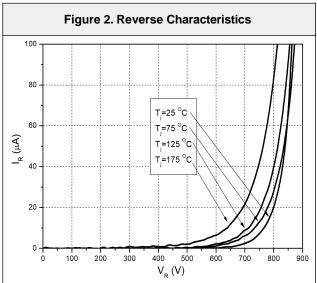
Package Marking and Ordering Information

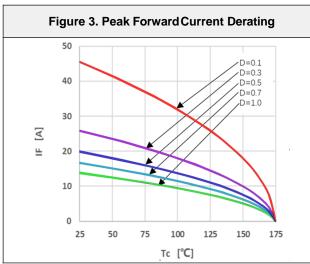
Part Number	Top Marking	Package	Packing Method	Quantity
BCH65S04D3	BCH65S04D3	TO220-2	Tube	50 units

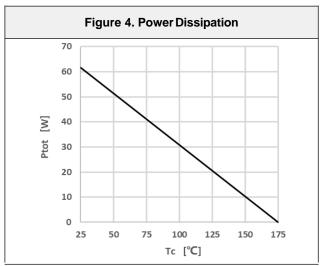


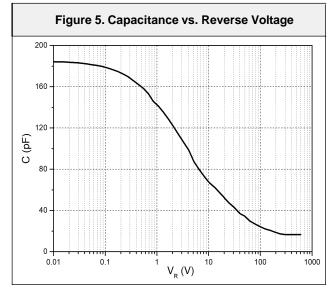
Typical Performance Characteristics

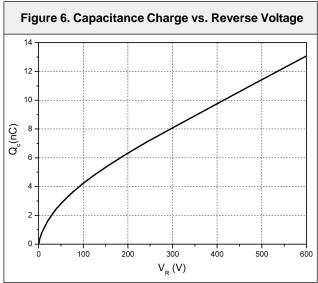






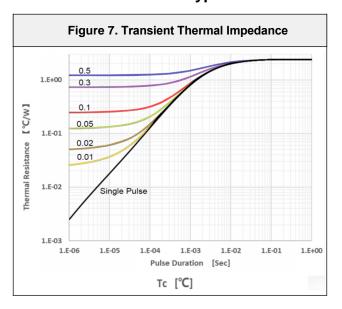








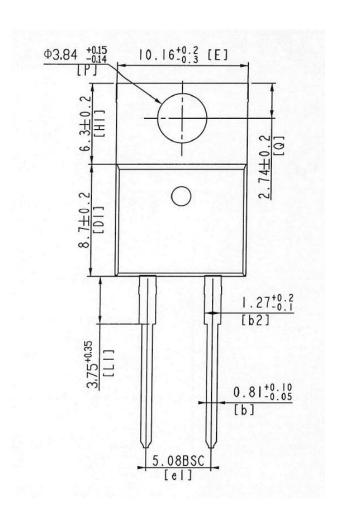
Typical Performance Characteristics

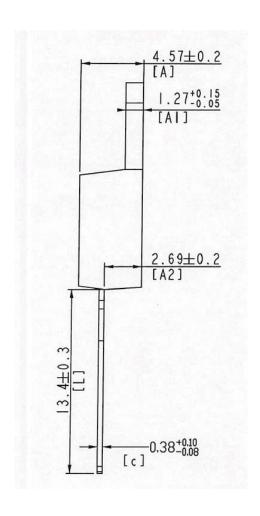




Package Outlines

TO220-2







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